2N6286 & 2N6287



PNP Darlington Power Silicon Transistor

Rev. V3

Features

- Available in JAN, JANTX and JANTXV per MIL-PRF-19500/505
- TO-3 (TO-204AA) Package
- Designed for General Purpose Amplifier and Low-Frequency Switching Applications



Electrical Characteristics

Parameter	Test Conditions	Symbol	Units	Min.	Max.		
					1		
Collector - Emitter Breakdown Voltage	I _C = -100 mA dc 2N6286 2N6287	V _{(BR)CEO}	V dc	-80 -100	_		
Collector - Emitter Cutoff Current	V_{CE} = -40 V dc, 2N6286 V_{CE} = -50 V dc, 2N6287	I _{CEO}	mA dc	_	-1.0		
Collector - Emitter Cutoff Current	V _{CE} = -80 V dc, V _{BE} = +1.5 V dc, 2N6286 V _{CE} = -100 V dc, V _{BE} = +1.5 V dc, 2N6287		μA dc	_	-10		
Emitter - Base Cutoff Current	V _{EB} = -7 V dc	I _{EBO}	mA dc	_	-2.5		
			1				
Forward Current Transfer Ratio	$V_{CE} = -3 \text{ V dc; } I_{C} = -1 \text{ A dc}$ Forward Current Transfer Ratio $V_{CE} = -3 \text{ V dc; } I_{C} = -10 \text{ A dc}$ $V_{CE} = -3 \text{ V dc; } I_{C} = -20 \text{ A dc}$		-	1,500 1,250 300	18,000		
Collector - Emitter Saturation Voltage	$I_C = -20 \text{ A dc}; I_B = -200 \text{ mA dc}$ $I_C = -10 \text{ A dc}; I_B = -40 \text{ mA dc}$	$V_{\text{CE(sat)1}} \ V_{\text{CE(sat)2}}$	V dc	_	-3.0 -2.0		
Base - Emitter Saturation Voltage	I_C = -20 A dc; I_B = -200 mA dc	V _{BE(sat)}	V dc	_	-4.0		
Base - Emitter Voltage	$V_{CE} = -3 \text{ V dc}; I_{C} = -10 \text{ A dc}$	V_{BE}	V dc	_	-2.8		
Collector - Emitter Cutoff Current	$T_A = +150^{\circ}\text{C}$ $V_{CE} = -80 \text{ V dc}, V_{BE} = +1.5 \text{ V dc}, 2N6286$ $V_{CE} = -100 \text{ V dc}, V_{BE} = +1.5 \text{ V dc}, 2N6287$	I _{CEX2}	mA dc	_	-5.0		
Collector - Emitter Saturation Voltage	$T_A = +150^{\circ}C$ $I_C = -10 \text{ A dc}; I_B = -40 \text{ mA dc}$	V _{CE(sat)3}	V dc	_	-2.0		
Forward Current Transfer Ratio	$T_A = -55^{\circ}C$ $V_{CE} = -3 \text{ V dc}; I_C = -10 \text{ A dc}$	h _{FE4}	-	150			
Dynamic Characteristics					'		
Magnitude of Common - Emitter Small-Signal Short-Circuit Forward - Current Transfer Ratio	V _{CE} = -3 V dc; I _C = -10 A dc; f = 1.0 MHz	h _{fe}	-	8	80		
Small-Signal Short-Circuit Forward - Current Transfer Ratio	$V_{CE} = -3 \text{ V dc}$; $I_{C} = -10 \text{ A dc}$; $f = 1.0 \text{ kHz}$	h _{fe}	-	300	_		
Open Circuit Output Capacitance	V _{CB} = -10 V dc; I _E = 0; 100 kHz ≤ f ≤ 1 MHz	C _{obo}	pF	_	400		
Switching Characteristics							
Turn-On Time	V_{CC} = -30 V dc; I_{C} = -10 A dc; I_{B} = -40 mA dc	t _{on}	μs	_	2.0		
Turn-Off Time	V_{CC} = -30 V dc; I_C = -10 A dc; I_{B1} = I_{B2} = -40 mA dc	t _{off}	μs	_	10		



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Rev. V3

Absolute Maximum Ratings (T_A = +25°C unless otherwise noted)

Ratings	Symbol	2N6286	2N6287	Units
Collector - Emitter Voltage	V _{CEO}	-80	-100	V dc
Collector - Base Voltage	V _{CBO}	-80	-100	V dc
Emitter - Base Voltage	V _{EBO}	-7		V dc
Collector Current	I _C	-20		A dc
Base Current	I _B	-0.5		A dc
Total Power Dissipation @ $T_C = +25^{\circ}C^{(1)}$ @ $T_C = +100^{\circ}C$	P _T	175 87.5		W
Operating & Storage Temperature Range	TJ, T _{STG}	-65 to +200		°C

⁽¹⁾ Derate linearly @ 1.16 W/ $^{\circ}$ C above $T_{\text{C}} > +25 ^{\circ}$ C.

Thermal Characteristics

Characteristics	Symbol	Max. Value
Thermal Resistance, Junction to Case	$R_{ heta JC}$	0.855°C/W

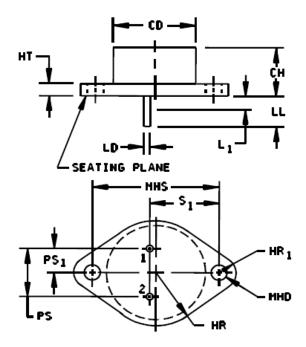
Safe Operating Area	
DC Tests:	T _C = +25 °C; t = 1.0 s; I Cycle
Test 1: Test 2: Test 3:	$V_{CE} = -8.75 \text{ V dc}$; $I_{C} = -20 \text{ A dc}$ $V_{CE} = -30 \text{ V dc}$; $I_{C} = -5.8 \text{ A dc}$ $V_{CE} = -80 \text{ Vdc}$; $I_{C} = -100 \text{ mA dc}$ 2N6286 $V_{CE} = -100 \text{ Vdc}$; $I_{C} = -100 \text{ mA dc}$ 2N6287



PNP Darlington Power Silicon Transistor

Rev. V3

Outline Drawing (TO-3)



NOTES:

- 1. Dimensions are in inches.
- 2. Millimeters are given for general information only.
- 3. Body contour is optional within zone defined by CD.
- These dimensions shall be measured at points .050 inch (1.27 mm) to .055 inch (1.40 mm) below seating plane.
- Both terminals.
- 6. At both ends.
- 7. Two holes.
- 8. Terminal 1 is the emitter, terminal 2 is base. The collector shall be electrically connected to the case.
- 9. LD applies between L₁ and LL. Diameter is uncontrolled in L₁.
- 10. In accordance with ASME Y14.5M, diameters are equivalent to φx symbology.

FIGURE 1. Physical dimensions (similar to TO-3).



PNP Darlington Power Silicon Transistor

Rev. V3

Outline Drawing (TO-3)

	Dimensions					
Symbol	Inches		Millimeters		Notes	
	Min	Max	Min	Max		
CD		.875		22.23	3	
СН	.250	.360	6.35	9.14		
HR	.495	.525	12.57	13.34		
HR ₁	.131	.188	3.33	4.78		
нт	.060	.135	1.52	3.43		
LD	.038	.043	0.97	1.09	5, 9	
LL	.312	.500	7.92	12.7	5	
L ₁		.050		1.27	5, 9	
MHD	.151	.165	3.84	4.19	7	
MHS	1.177	1.197	29.90	30.40		
PS	.420	.440	10.67	11.18	4	
PS ₁	.205	.225	5.21	5.72		
S ₁	.655	.675	16.64	17.15		

FIGURE 1. Physical dimensions (similar to TO-3) - Continued.

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Rev. V3

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